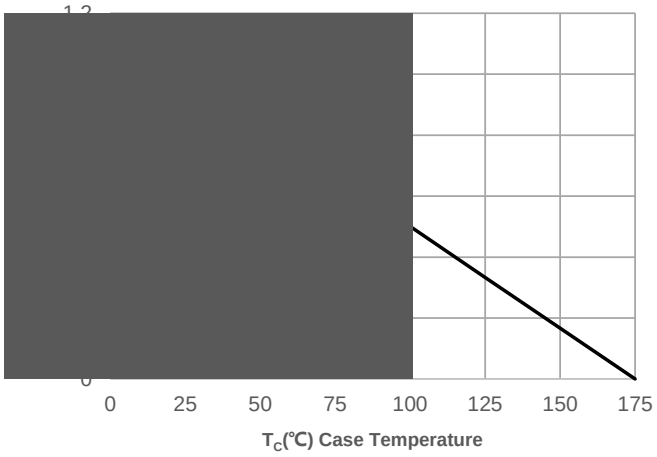
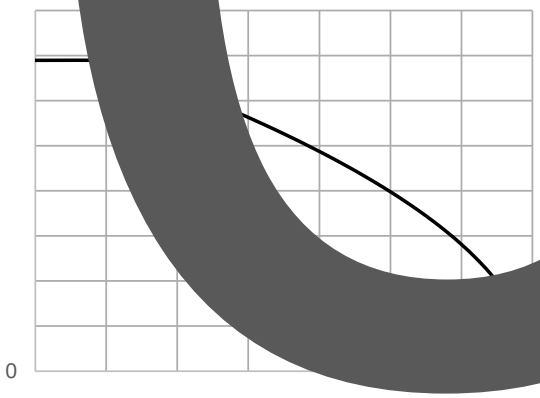
Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit
Off Characteristics				
$V_{(BR)DSS}$	40	-	-	V
I_{DSS}	-	-	1.0	A
I_{GSS}	-	-	±100	nA
$V_{GS(th)}$	2.0	2.8	4.0	V
	-	0.65	0.8	m
R_g	-	2.1	-	
C_{iss}	-	7655	10340	pF
C_{oss}	-	1925	2600	pF
C_{rss}	-	95	200	pF
Q_g	-	111	-	nC
Q_{gs}	-	35	-	nC
Q_{gd}	-	19	-	nC
$t_{d(on)}$	-	22	-	ns
t_r	-	38	-	ns
$t_{d(off)}$	-	76	-	ns
t_f	-	29	-	ns
I_S	-	-	345	A
I_{SM}	-	-	1380	A
V_{SD}	-		1.2	V
trr	28	57	85	ns
Qrr				

Typical Performance Characteristics

Figure 1: Power De-rating





Typical Performance Characteristics

Figure 5: Output Characteristics

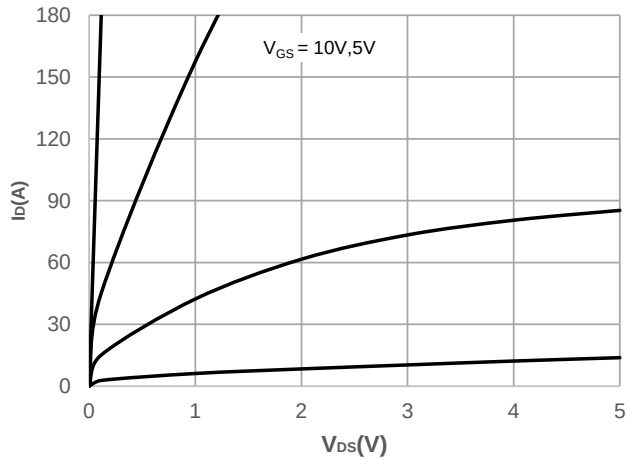


Figure 6: Typical Transfer Characteristics

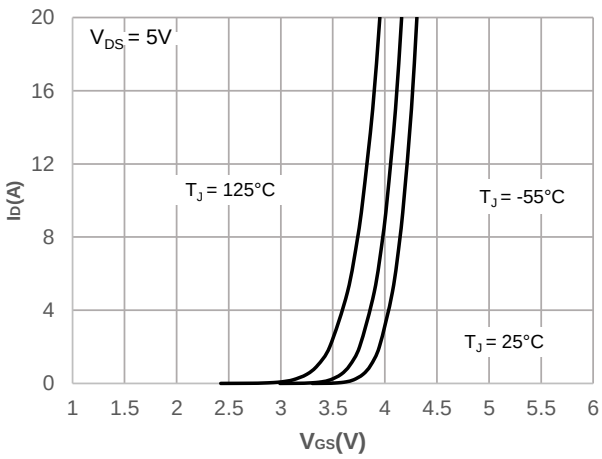


Figure 7: On-resistance vs. Drain Current

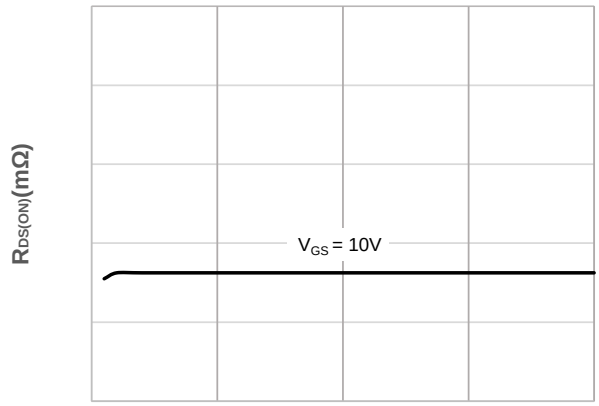


Figure 8: Body Diode Characteristics

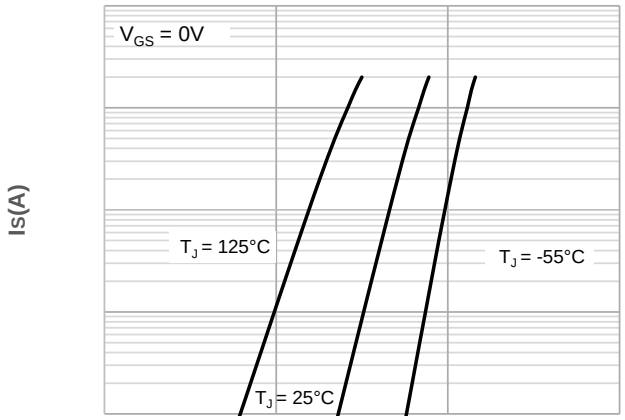
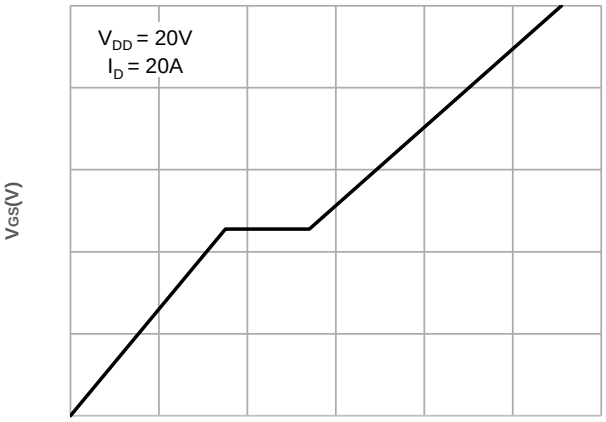
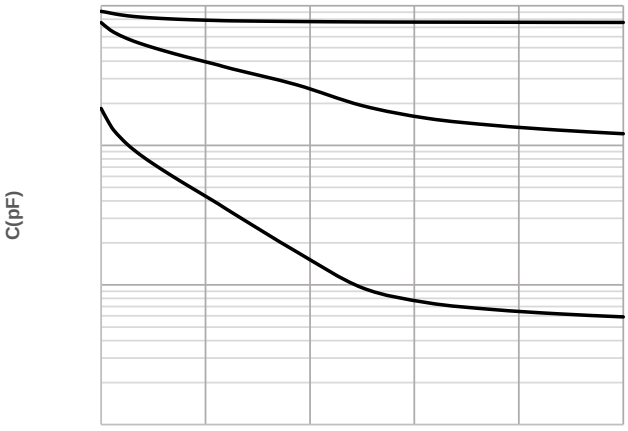


Figure 9: Gate Charge Characteristics





Typical Performance Characteristics

Figure 11: Normalized Breakdown Voltage vs. Junction Temperature

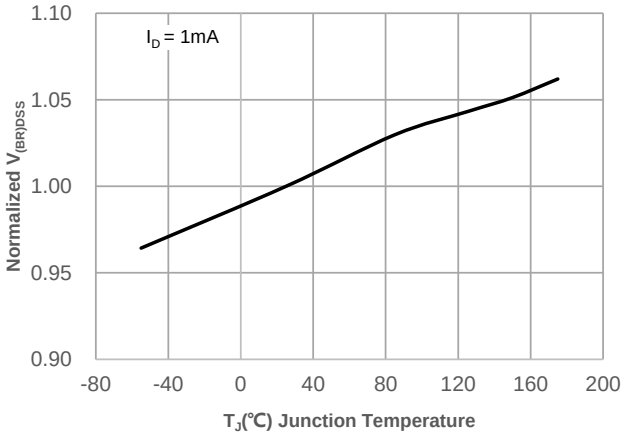
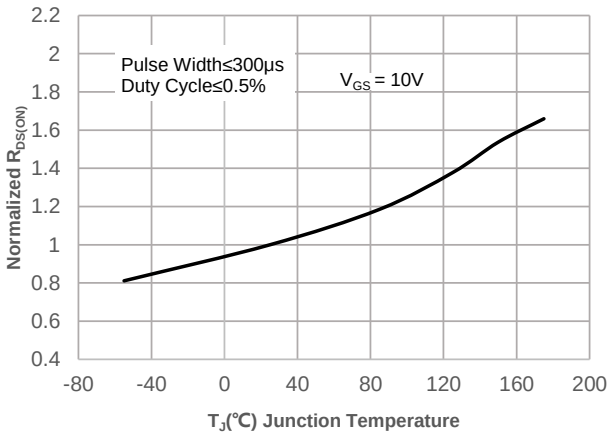


Figure 12: Normalized on Resistance vs. Junction Temperature



Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform

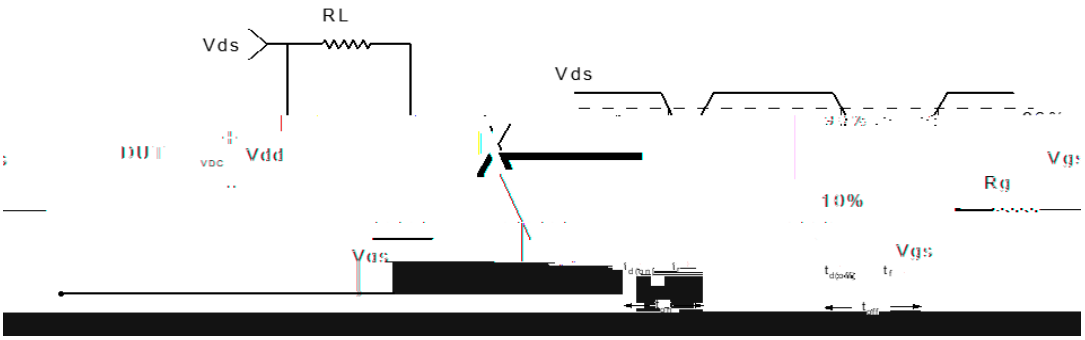


Figure 2: Resistive Switching Test Circuit & Waveform

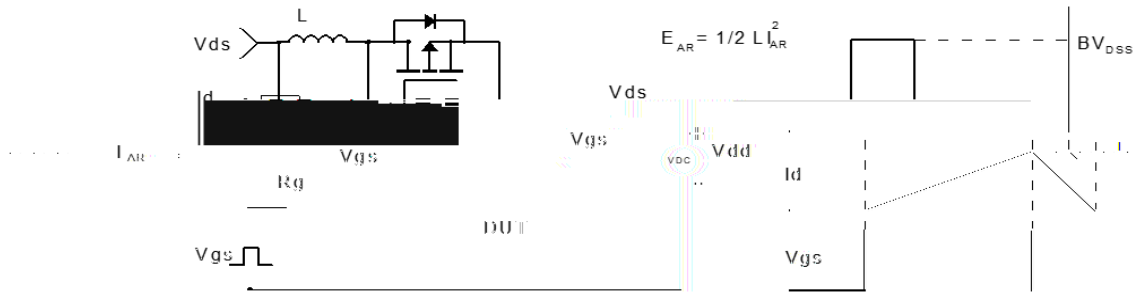


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

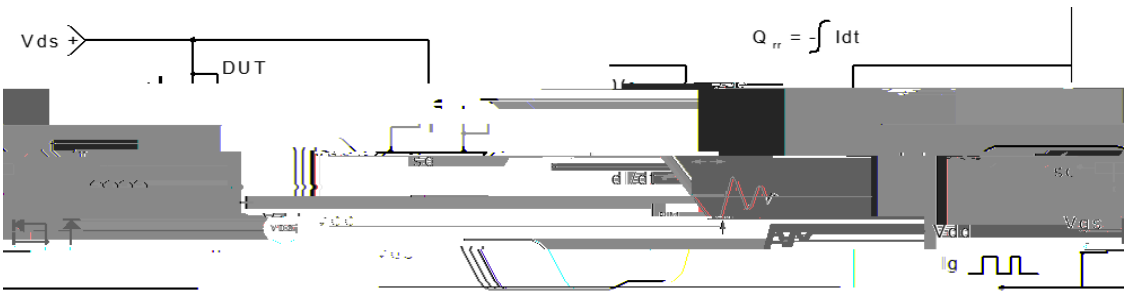


Figure 4: Diode Recovery Test Circuit & Waveform

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Package Mechanical Data(PDFN5X6-8L)

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